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SLLS708A - JANUARY 2006-REVISED SEPTEMBER 2009

3-V TO 5.5-V MULTICHANNEL RS-232 LINE DRIVER/RECEIVER WITH ±15-kV ESD PROTECTION

Check for Samples: MAX3222E

FEATURES

- ESD Protection for RS-232 Bus Pins
 - ±15-kV Human-Body Model (HBM)
 - ±8-kV IEC61000-4-2, Contact Discharge
 - ±15-kV IEC61000-4-2, Air-Gap Discharge
- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operates With 3-V to 5.5-V V_{CC} Supply
- Operates up to 500 kbit/s
- Two Drivers and Two Receivers
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 × 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply
- Alternative High-Speed Pin-Compatible Device (1 Mbit/s) for SNx5C3222E

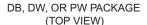
APPLICATIONS

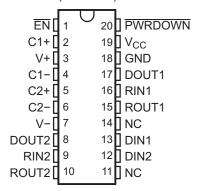
- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

DESCRIPTION/ORDERING INFORMATION

The MAX3222E consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND).

The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at typical data signaling rates up to 500 kbit/s and a maximum of 30-V/µs driver output slew rate.





NC - No internal connection

The MAX3222E can be placed in the power-down mode by setting the power-down ($\overline{PWRDOWN}$) input low, which draws only 1 μA from the power supply. When the device is powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V_{CC} , and V_{CC} is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable (\overline{EN}) high.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



ORDERING INFORMATION

T _A	PACK	AGE ^{(1) (2)}	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC - DW	Tube of 25	MAX3222ECDW	MAX3222EC
	SOIC - DW	Reel of 2000	MAX3222ECDWR	WIAA3222EC
0°C to 70°C	SSOP – DB	Tube of 70	MAX3222ECDB	MP222EC
0.0 10 10.0	330P - DB	Reel of 2000	MAX3222ECDBR	WIP222EC
	TSSOP – PW	Tube of 70	MAX3222ECPW	MP222EC
	1550P – PW	Reel of 2000	MAX3222ECPWR	WIP222EC
	SOIC - DW	Tube of 25	MAX3222EIDW	MAX3222EI
	SOIC - DW	Reel of 2000	MAX3222EIDWR	IVIAA3222EI
40°C to 05°C	SSOP – DB	Tube of 70	MAX3222EIDB	MP222EI
–40°C to 85°C	330P - DB	Reel of 2000	MAX3222EIDBR	WIP222EI
	TOOD DW	Tube of 70	MAX3222EIPW	MP222EI
	TSSOP – PW Reel of 2000		MAX3222EIPWR	WIPZZZEI

- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

Table 1. FUNCTION TABLES

EACH DRIVER(1)

INPUTS		OUTPUT
DIN	PWRDOWN	DOUT
Х	L	Z
L	Н	Н
Н	Н	L

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Table 2. EACH RECEIVER⁽¹⁾

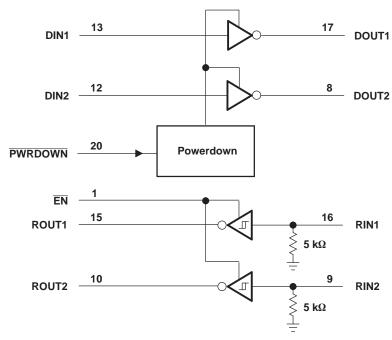
INPUTS		OUTPUT
RIN	EN	ROUT
L	L	Н
Н	L	L
X	Н	Z
Open	L	Н

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off),

Open = input disconnected or connected driver off



LOGIC DIAGRAM (POSITIVE LOGIC)



Pin numbers are for the DB, DW, and PW packages.

ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

		·	MIN	MAX	UNIT
V _{CC}	Supply voltage range (2)		-0.3	6	V
V+	Positive-output supply voltage range (2)		-0.3	7	V
V-	Negative-output supply voltage range (2)		0.3	-7	V
V+ - V-	Supply voltage difference ⁽²⁾			13	V
VI	land to the management	Driver (EN, PWRDOWN)	-0.3	6	\ /
	Input voltage range	Receiver	-25	25	V
V	Output voltage range	Driver	-13.2	13.2	V
Vo		Receiver	-0.3	V _{CC} + 0.3	V
		DB package		70	
θ_{JA}	Package thermal impedance (3) (4)	DW package		58	°C/W
		PW package		83	
T_J	Operating virtual junction temperature			150	°C
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ All voltages are with respect to network GND.

⁽³⁾ Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

⁽⁴⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



RECOMMENDED OPERATING CONDITIONS(1)

See Figure 5

				MIN	NOM	MAX	UNIT
	Supply voltage		V _{CC} = 3.3 V	3	3.3	3.6	V
			V _{CC} = 5 V	4.5	5	5.5	V
V	Driver and control high-level input voltage DIN, EN, PWRDOWN	$V_{CC} = 3.3 \text{ V}$	2			V	
V_{IH}		DIN, EN, PWKDOWN	$V_{CC} = 5 V$	2.4			V
V_{IL}	Driver and control low-level input voltage	DIN, EN, PWRDOWN				0.8	V
V_{I}	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	V
V_{I}	Receiver input voltage		-25		25	V	
т	Operating free-air temperature		MAX3222EC	0		70	°C
IA			MAX3222EI	-40		85	C

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.

ELECTRICAL CHARACTERISTICS(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CONDITIONS	MIN TY	⁽²⁾ MAX	UNIT
I	Input leakage current (EN, PWRDOWN)		±(0.01 ±1	μΑ
I _{CC}	Supply current	No load, PWRDOWN at V _{CC}		0.3 1	mA
	Supply current (powered off)	No load, PWRDOWN at GND		1 10	μΑ

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.



DRIVER SECTION

Electrical Characteristics (1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.4		V
V _{OL}	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = V _{CC}	- 5	-5.4		V
I _{IH}	High-level input current	$V_I = V_{CC}$			±0.01	±1	μΑ
I_{IL}	Low-level input current	V _I at GND			±0.01	±1	μΑ
laa	Short-circuit output current (3)	V _{CC} = 3.6 V	V _O = 0 V		±35	±60	mA
Ios	Short-circuit output current	$V_{CC} = 5.5 \text{ V}$	v0 = 0 v		±33	±00	ША
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	$V_O = \pm 2 V$	300	10M		Ω
	Output leakage current	PWRDOWN = GND	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$ $V_{O} = \pm 12 \text{ V}$			±25	
l _{OZ}		Output leakage current PWRDOWN = GND	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V},$ $V_{O} = \pm 10 \text{ V}$			±25	μA

- Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.
- All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST	CONDITIONS	MIN	TYP (2)	MAX	UNIT
	Maximum data rate	C _L = 1000 pF, One DOUT switching,	$R_L = 3 \text{ k}\Omega,$ See Figure 1	250	500		kbit/s
t _{sk(p)}	Pulse skew ⁽³⁾	$C_L = 150 \text{ pF to } 2500 \text{ pF},$ See Figure 2	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$		300		ns
	Slew rate,	$R_1 = 3 k\Omega$ to $7 k\Omega$,	C _L = 150 pF to 1000 pF	6		30	
SR(tr)	transition region (see Figure 1)	$V_{CC} = 3.3 \text{ V}$	C _L = 150 pF to 2500 pF	4		30	V/µs

- Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. Pulse skew is defined as $|t_{PLH} t_{PHL}|$ of each channel of the same device.

ESD Protection

		TYP	UNIT
	Human-Body Model (HBM)	±15	
Driver outputs (DOUTx)	IEC61000-4-2, Air-Gap Discharge	±15	kV
	IEC61000-4-2, Contact Discharge	±8	

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RECEIVER SECTION

Electrical Characteristics (1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = −1 mA	V _{CC} - 0.6	V _{CC} - 0.1		V
V_{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V	Positive-going input threshold voltage	$V_{CC} = 3.3 \text{ V}$		1.5	2.4	V
V _{IT+}	Positive-going input tilleshold voltage	V _{CC} = 5 V		1.8	2.4	
V	Negative going input threehold veltage	$V_{CC} = 3.3 \text{ V}$	0.6	1.2		V
V _{IT}	Negative-going input threshold voltage	$V_{CC} = 5 V$	0.8	1.5		V
V_{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
l _{OZ}	Output leakage current	EN = 1		±0.05	±10	μA
r _i	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V. All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP ⁽²⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF, See Figure 3	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF, See Figure 3	300	ns
t _{en}	Output enable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega, \text{ See Figure 4}$	200	ns
t _{dis}	Output disable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega, \text{ See Figure 4}$	200	ns
t _{sk(p)}	Pulse skew ⁽³⁾	See Figure 3	300	ns

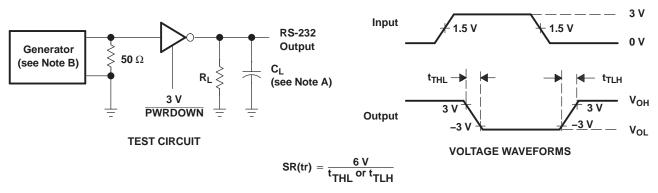
⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. (3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

ESD Protection

		TYP	UNIT
	Human-Body Model (HBM)	±15	
Receiver inputs (RINx)	IEC61000-4-2, Air-Gap Discharge	±15	kV
	IEC61000-4-2, Contact Discharge	±8	

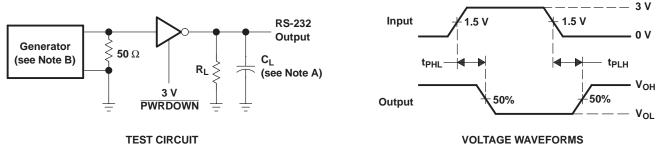


PARAMETER MEASUREMENT INFORMATION



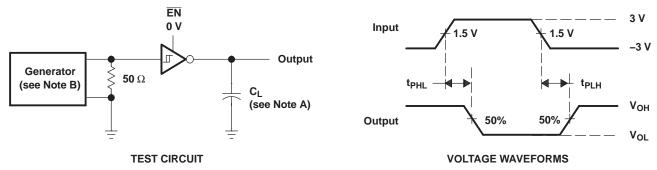
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 1. Driver Slew Rate



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew

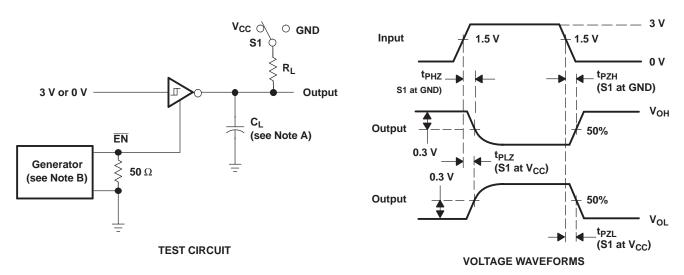


- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 3. Receiver Propagation Delay Times



PARAMETER MEASUREMENT INFORMATION (continued)

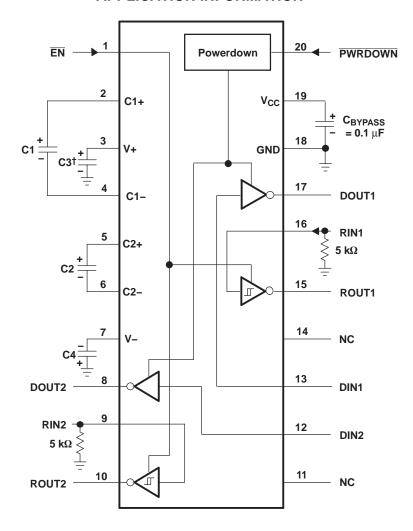


- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: Z_O = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 4. Receiver Enable and Disable Times



APPLICATION INFORMATION



 † C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

- B. NC No internal connection
- C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V _{CC}	C1	C2, C3, and C4			
3.3 V \pm 0.3 V	0.1 μ F	0.1 μ F			
5 V ± 0.5 V	0.047 μ F	0.33 μ F			
3 V to 5.5 V	0.1 μ F	0.47 μ F			

Figure 5. Typical Operating Circuit and Capacitor Values





6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
MAX3222ECDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC	Samples
MAX3222ECDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC	Samples
MAX3222ECDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3222EC	Samples
MAX3222ECDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3222EC	Samples
MAX3222ECPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC	Samples
MAX3222ECPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC	Samples
MAX3222ECPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC	Samples
MAX3222EIDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI	Samples
MAX3222EIDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI	Samples
MAX3222EIDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3222EI	Samples
MAX3222EIDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3222EI	Samples
MAX3222EIPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI	Samples
MAX3222EIPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI	Samples
MAX3222EIPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

6-Feb-2020

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





Α0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX3222ECDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3222ECDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3222ECPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
MAX3222EIDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3222EIDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3222EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
MAX3222ECDBR	SSOP	DB	20	2000	367.0	367.0	38.0
MAX3222ECDWR	SOIC	DW	20	2000	367.0	367.0	45.0
MAX3222ECPWR	TSSOP	PW	20	2000	367.0	367.0	38.0
MAX3222EIDBR	SSOP	DB	20	2000	367.0	367.0	38.0
MAX3222EIDWR	SOIC	DW	20	2000	367.0	367.0	45.0
MAX3222EIPWR	TSSOP	PW	20	2000	367.0	367.0	38.0



SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
 C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SOIC



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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